

TSM4435

30V P-Channel MOSFET



SOP-8



Pin Definition:

- 1. Source
- 2. Source
- 3. Source

4. Gate 5, 6, 7, 8. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
-30	21 @ V _{GS} = -10V	-9.1	
	35 @ V _{GS} = -4.5V	-6.9	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

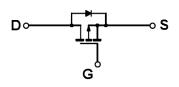
Application

- DC-DC Conversion
- Battery Switch

Ordering Information

Part No.	Package	Packing
TSM4435CS RL	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		l _D	-9.1	Α	
Pulsed Drain Current	urrent I _{DM}		-50	Α	
Continuous Source Current (Diode Continuo Sourc	nduction) ^{a,b}	I _S	-2.1	Α	
Maximum Power Dissipation	Ta = 25°C	Ь	2.5	W	
	Ta = 75°C	P _D	1.6		
Operating Junction Temperature	re T _J +150		+150	°C	
Operating Junction and Storage Temp	erature Range	Range T _J , T _{STG} - 55 to +150		°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	RO _{JF}	22	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	50	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.



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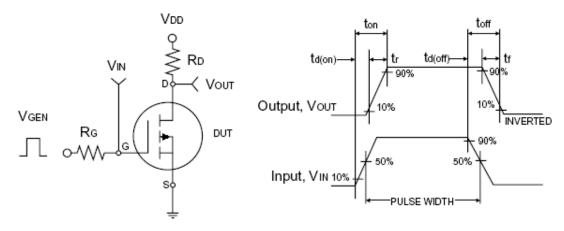


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static		1				l
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1		-3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}	1		±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I _{DSS}			-1.0	μΑ
On-State Drain Current ^a	$V_{DS} = -5V, V_{GS} = -10V$	I _{D(ON)}	-40			Α
Drain Course On State Desistance	$V_{GS} = -10V, I_D = -9.1A$			17	21	mΩ
Drain-Source On-State Resistance ^a	$V_{GS} = -4.5V$, $I_D = -6.9A$	R _{DS(ON)}		25	35	
Forward Transconductance ^a	$V_{DS} = -10V, I_{D} = -9.1A$	9 _{fs}		24		S
Diode Forward Voltage	$I_S = -2.1A$, $V_{GS} = 0V$	V_{SD}		-0.8	-1.2	V
Dynamic ^b						
Total Gate Charge	\/ - 15\/ - 0.10	Q_g		33	70	
Gate-Source Charge	$V_{DS} = -30V, V_{GS} = 0V$ $V_{DS} = -5V, V_{GS} = -10V$ $V_{GS} = -10V, I_D = -9.1A$ $V_{GS} = -4.5V, I_D = -6.9A$ $V_{DS} = -10V, I_D = -9.1A$	Q_{gs}		5.8		nC
Gate-Drain Charge	V _{GS} = -10V	Q_{gd}	I	8.6		
Input Capacitance	\\ - 45\\ \\ - 0\\	C _{iss}		1573	1900	
Output Capacitance	, 55	C _{oss}		319		pF
Reverse Transfer Capacitance	1 = 1.0WIDZ	C _{rss}		211	295	
Switching ^c						
Turn-On Delay Time	V 45V D 450	t _{d(on)}		10	15	
Turn-On Rise Time		t _r		15	25	
Turn-Off Delay Time	$I_D = -1A$, $V_{GEN} = -10V$,	t _{d(off)}		110	170	nS
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		70	110	

Notes:

- a. pulse test: PW $\leq 300 \mu S$, duty cycle $\leq 2\%$ b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

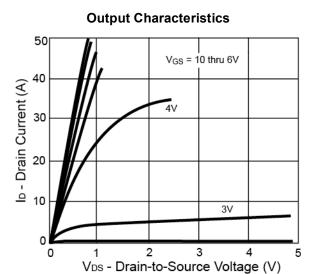




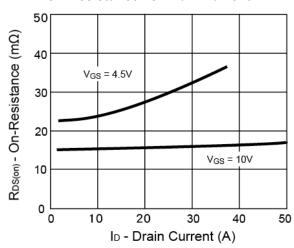




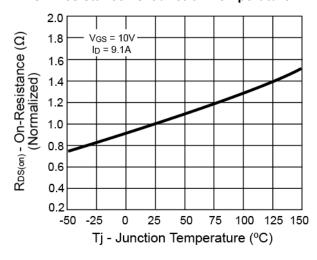
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



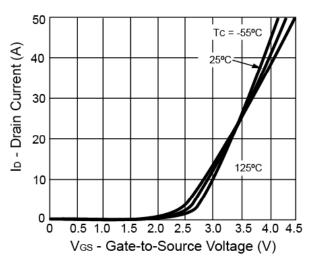
On-Resistance vs. Drain Current



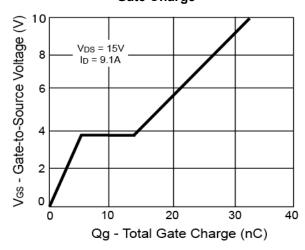
On-Resistance vs. Junction Temperature



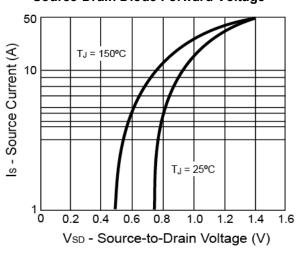
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage





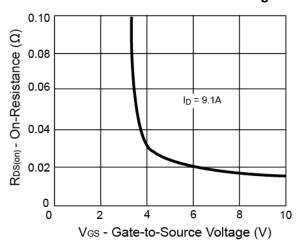


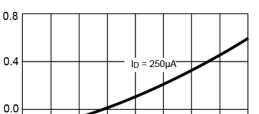




Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

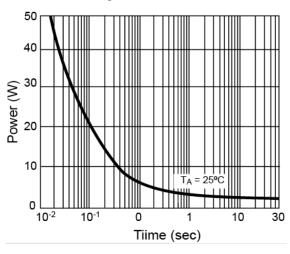




Threshold Voltage

-25 0 25 50 75 100 125 150 Tj - Junction Temperature (°C)

Single Pulse Power



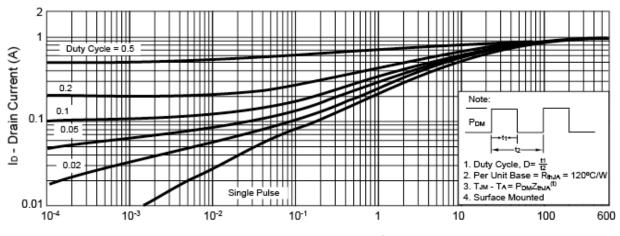
Normalized Thermal Transient Impedance, Junction-to-Ambient

Vgs(th) - Variance (V)

-0.4

-0.8

-50



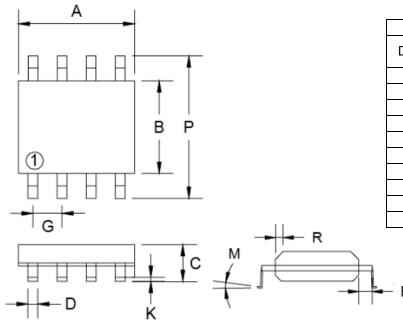
Square Wave Pulse Duration (sec)







SOP-8 Mechanical Drawing



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27BSC		0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



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